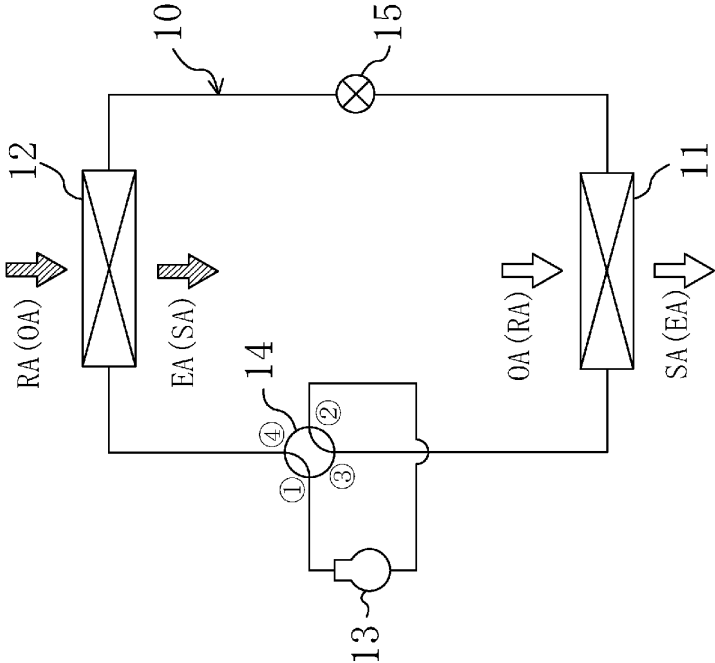
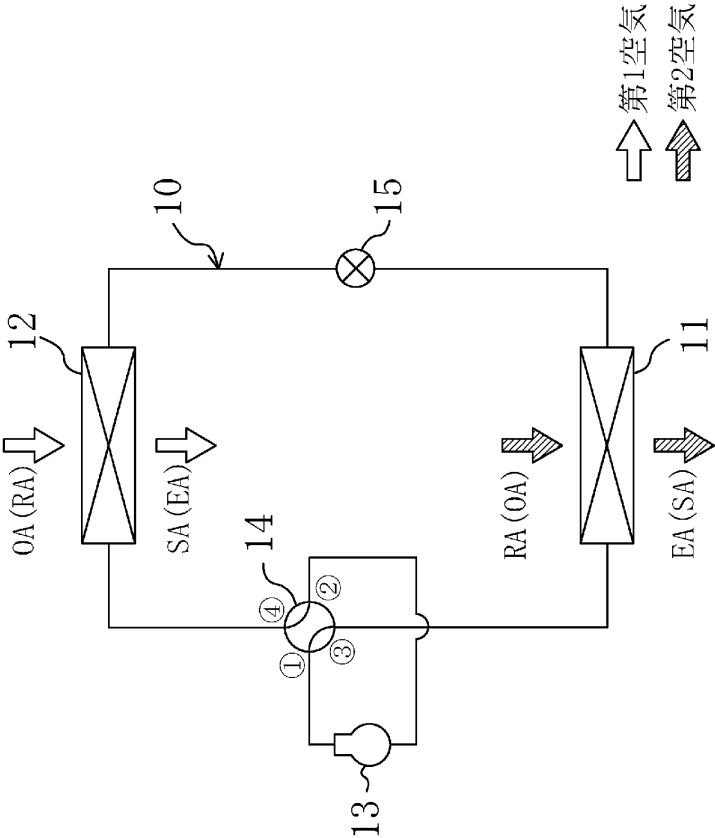


[図1]

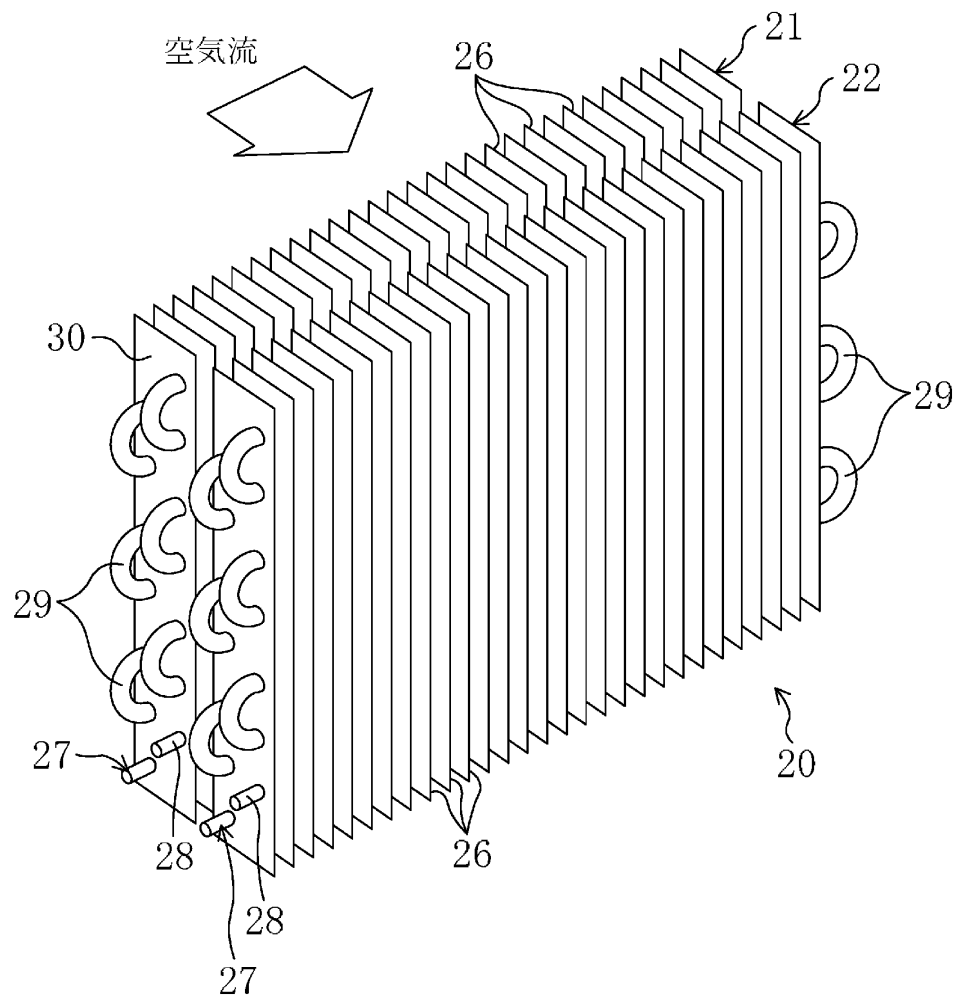
(B) 第2動作



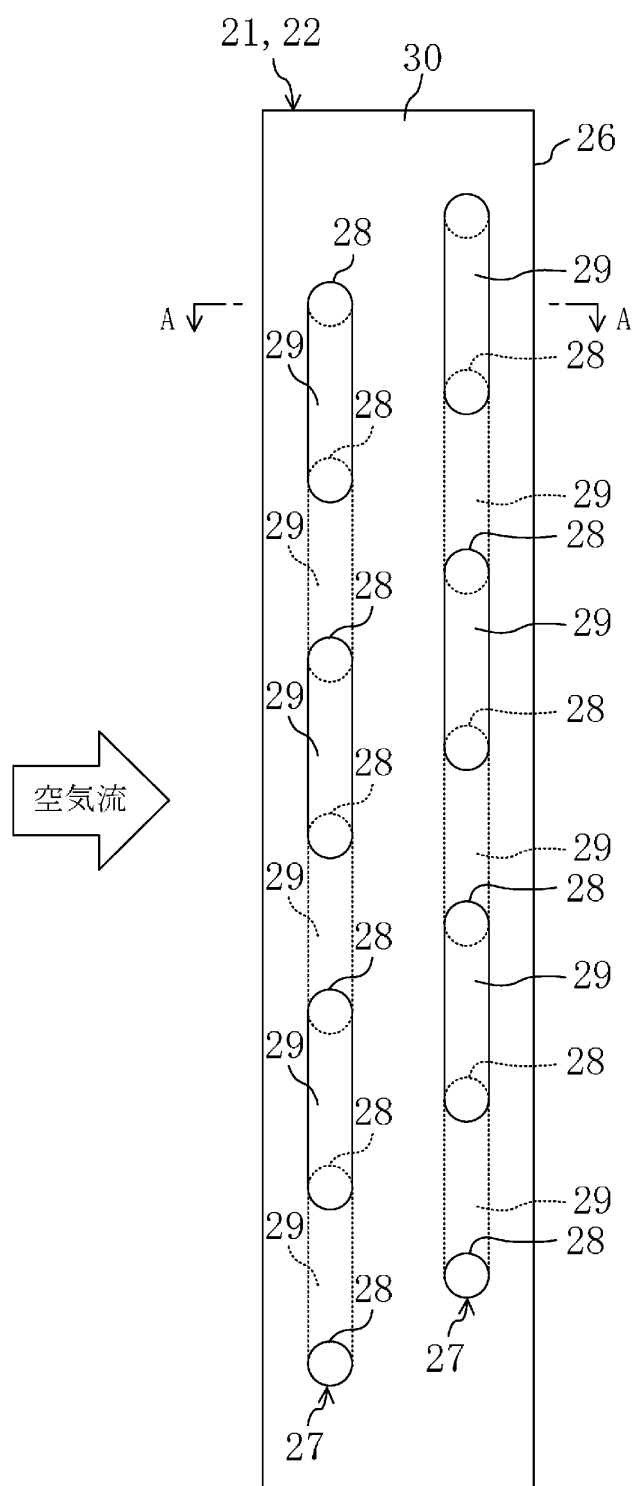
(A) 第1動作



[図2]



[図3]



A cross-sectional view of a semiconductor device. It shows a substrate 26 with diagonal hatching. Above the substrate is a thin layer 42. On top of layer 42 is a layer 41, which contains four circular features. A bracket on the right groups layers 41 and 42 as part of a larger structure 30.

30

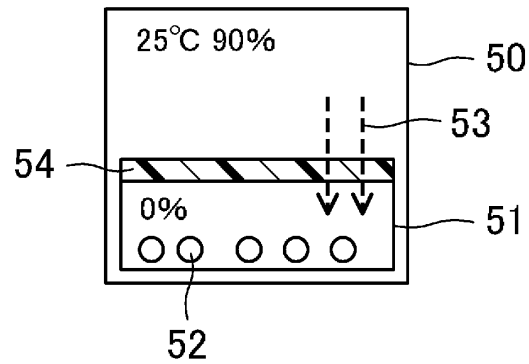
41

42

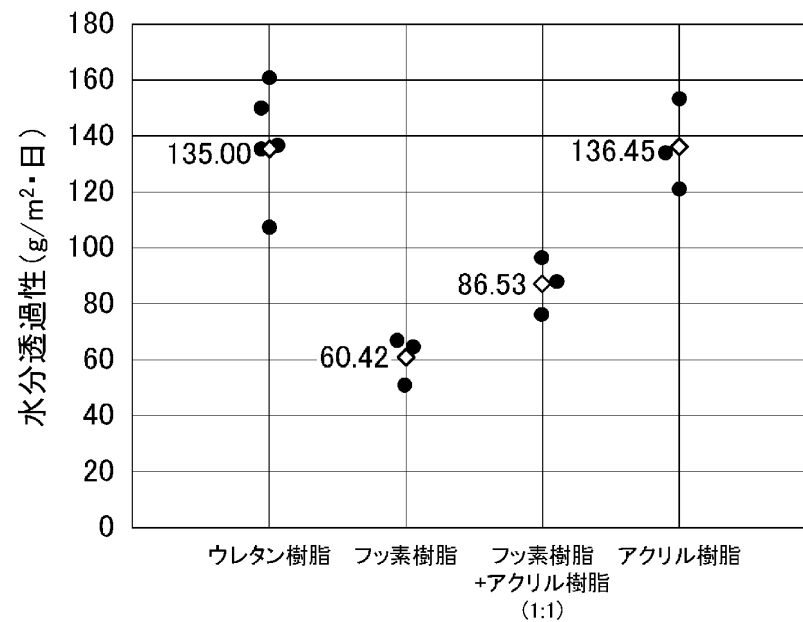
43

26

[図7]



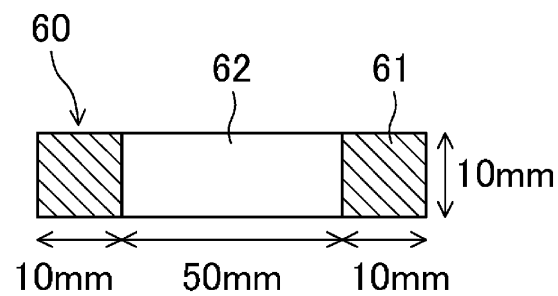
[図8]



吸着熱交換器能力 (100%) 84.8% 89.7% 90.2%

(相対値)

[図9]



[図10]

